



## N-Channel Depletion-Mode DMOS FET

### Features

- ▶ Free from secondary breakdown
- ▶ Low power drive requirement
- ▶ Ease of paralleling
- ▶ Excellent thermal stability
- ▶ Integral source-drain diode
- ▶ High input impedance and low  $C_{ISS}$
- ▶ ESD gate protection

### Applications

- ▶ Solid state relays
- ▶ Normally-on switches
- ▶ Converters
- ▶ Power supply circuits
- ▶ Constant current sources
- ▶ Input protection circuits

### General Description

The LND250 is a high voltage N-channel depletion mode (normally-on) transistor utilizing Supertex's lateral DMOS technology. The gate is ESD protected.

The LND250 is ideal for high voltage applications in the areas of normally-on switches, precision constant current sources, voltage ramp generation and amplification.

### Ordering Information

Part Number	Package Options	Packing
LND250K1-G*	TO-236AB (SOT-23)	3000/Reel

-G denotes a lead (Pb)-free / RoHS compliant package

\* Part is not recommended for new designs. Please refer to LND150K1-G.

### Product Summary

$BV_{DSX}/BV_{DGX}$ (V)	$R_{DS(ON)}$ (max)	$I_{DSS}$ (min)
500	1.0k $\Omega$	1.0mA

### Absolute Maximum Ratings

Parameter	Value
Drain-to-source	$BV_{DSX}$
Drain-to-gate	$BV_{DGX}$
Gate-to-source	$\pm 20V$
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

### Pin Configuration



TO-236AB (SOT-23)

### Product Marking

**NDEW** W = Code for Week Sealed  
 \_\_\_\_\_ = "Green" Packaging

TO-236AB (SOT-23)

Packages may or may not include the following marks: Si or

## Thermal Characteristics

Package	$I_D$ (continuous) <sup>†</sup> (mA)	$I_D$ (pulsed) (mA)	Power Dissipation @ $T_A = 25^\circ\text{C}$ (W)	$\theta_{ja}$ ( $^\circ\text{C}/\text{W}$ )	$I_{DR}$ (mA)	$I_{DRM}^{\dagger}$ (mA)
TO-236AB (SOT-23)	13	30	0.36	203	13	30

### Notes:

<sup>†</sup>  $I_D$  (continuous) is limited by max rated  $T_j$ .

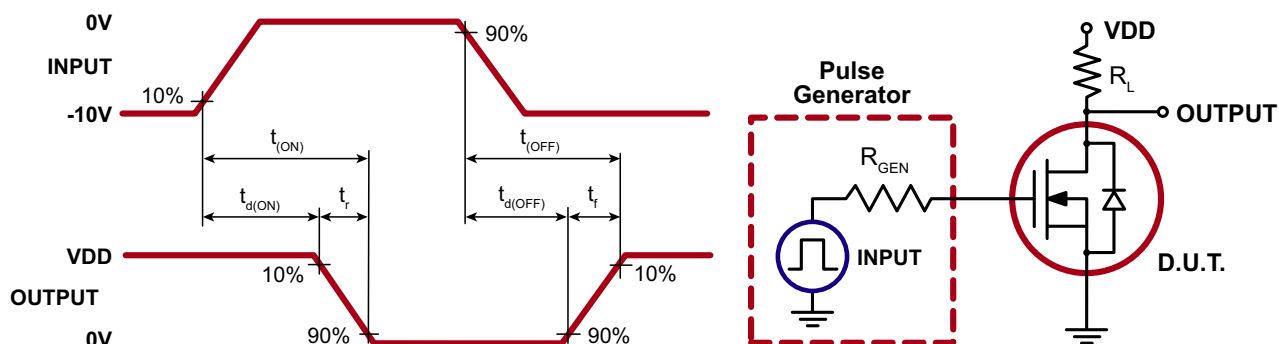
## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
$BV_{DSX}$	Drain-to-source breakdown voltage	500	-	-	V	$V_{GS} = -10\text{V}$ , $I_D = 1.0\text{mA}$
$V_{GS(OFF)}$	Gate-to-source off voltage	-1.0	-	-3.0	V	$V_{GS} = 25\text{V}$ , $I_D = 100\text{nA}$
$\Delta V_{GS(OFF)}$	Change in $V_{GS(OFF)}$ with temperature	-	-	5.0	mV/ $^\circ\text{C}$	$V_{GS} = 25\text{V}$ , $I_D = 100\text{nA}$
$I_{GSS}$	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
$I_{D(OFF)}$	Drain-to-source leakage current	-	-	100	nA	$V_{GS} = -10\text{V}$ , $V_{DS} = 450\text{V}$
		-	-	100	$\mu\text{A}$	$V_{DS} = 0.8\text{V}$ Max Rating, $V_{GS} = -10\text{V}$ , $T_A = 125^\circ\text{C}$
$I_{DSS}$	Saturated drain-to-source current	1.0	-	3.0	mA	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	850	1000	$\Omega$	$V_{GS} = 0\text{V}$ , $I_D = 0.5\text{mA}$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.2	%/ $^\circ\text{C}$	$V_{GS} = 0\text{V}$ , $I_D = 0.5\text{mA}$
$G_{FS}$	Forward transductance	1.0	2.0	-	mmho	$V_{DS} = 0\text{V}$ , $I_D = 1.0\text{mA}$
$C_{ISS}$	Input capacitance	-	7.5	10	pF	$V_{GS} = -10\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1.0\text{MHz}$
$C_{OSS}$	Common source output capacitance	-	2.0	3.5		
$C_{RSS}$	Reverse transfer capacitance	-	0.5	1.0		
$t_{d(ON)}$	Turn-on delay time	-	0.09	-	$\mu\text{s}$	$V_{DD} = 25\text{V}$ , $I_D = 1.0\text{mA}$ , $R_{GEN} = 25\Omega$
$t_r$	Rise time	-	0.45	-		
$t_{d(OFF)}$	Turn-off delay time	-	0.1	-		
$t_f$	Fall time	-	1.3	-		
$V_{SD}$	Diode forward voltage drop	-	-	0.9	V	$V_{GS} = -10\text{V}$ , $I_{SD} = 1.0\text{mA}$
$t_{rr}$	Reverse recovery time	-	200	-	ns	$V_{GS} = -10\text{V}$ , $I_{SD} = 1.0\text{mA}$

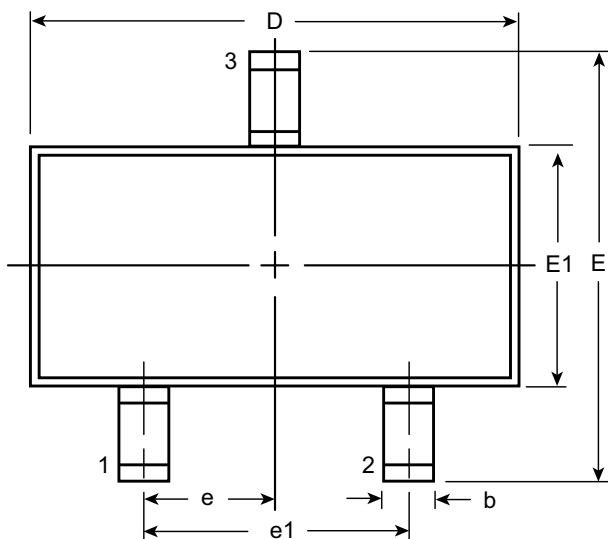
### Notes:

- All D.C. parameters 100% tested at  $25^\circ\text{C}$  unless otherwise stated. (Pulse test:  $300\mu\text{s}$  pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

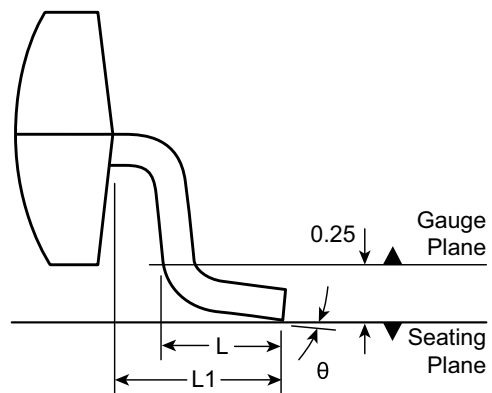
## Switching Waveforms and Test Circuit



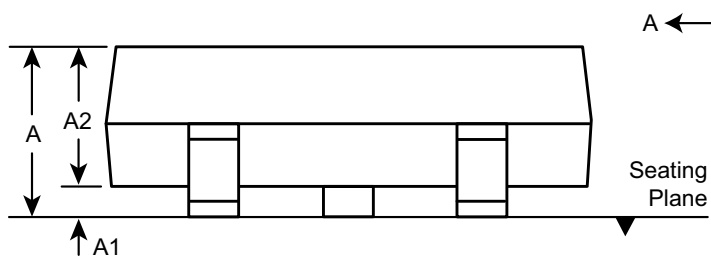
### 3-Lead TO-236AB (SOT-23) Package Outline (K1) 2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



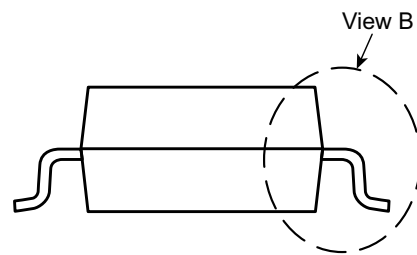
**Top View**



**View B**



**Side View**



**View A - A**

Symbol	A	A1	A2	b	D	E	E1	e	e1	L	L1	$\theta$	
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.95 BSC	1.90 BSC	0.20 <sup>†</sup>	0.54 REF	0°
	NOM	-	-	0.95	-	2.90	-	1.30			0.50		-
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40			0.60		8°

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

<sup>†</sup> This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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